TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

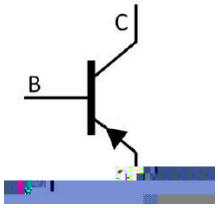
Features

High voltage.

Application

High voltage control circuit.

Internal Circuit



Package Outline



PIN1 Collector PIN 2 Base PIN 3 Emitter

Marking

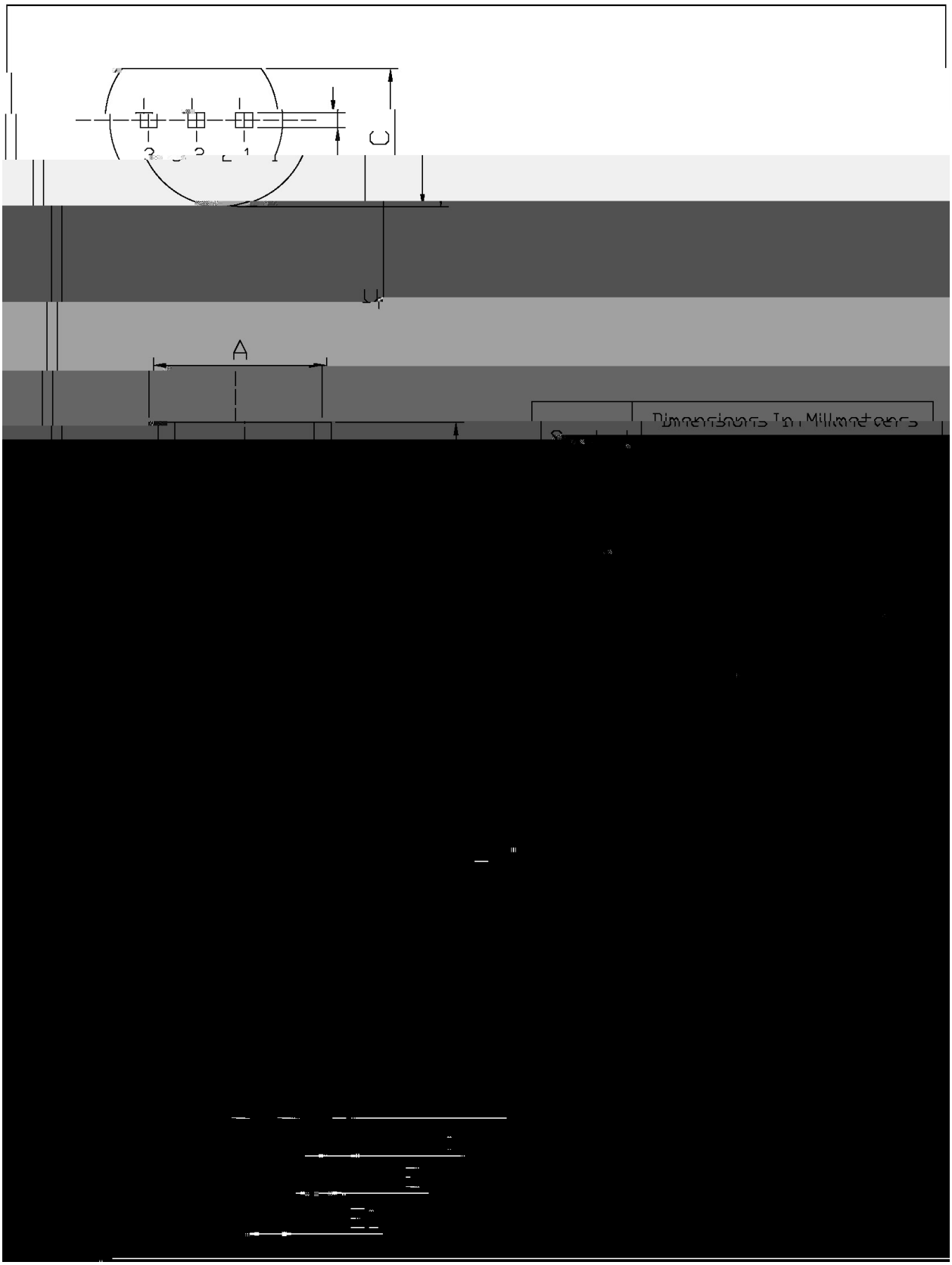
See Marking Instructions.

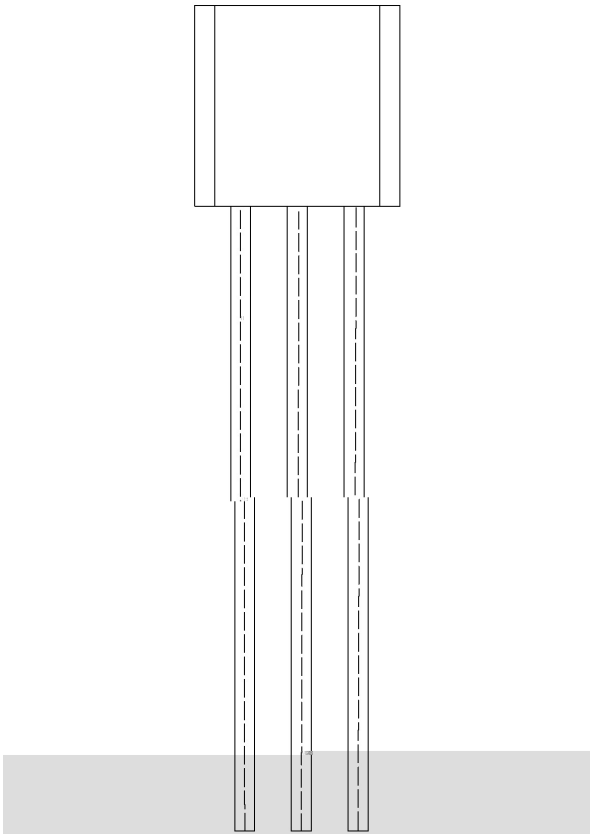
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-400	V
Collector to Emitter Voltage	V_{CEO}	-400	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-300	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA I_E=0	-400			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-400			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-100μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-300V I_E=0			-0.1	μA
Collector Cut-Off Current	I_{CES}	V_{CE}=-400V V_{BE}=0			-1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-10V I_C=-10mA	80		300	
	$h_{FE(2)}$	V_{CE}=-10V I_C=-1.0mA	70			
	$h_{FE(3)}$	V_{CE}=-10V I_C=-100mA	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=-10mA I_B=-1.0mA			-0.2	V
	$V_{CE(sat)(2)}$	I_C=-50mA I_B=-5.0mA			-0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-10mA I_B=-1.0mA			-0.75	V
Transition Frequency	f_T	V_{CE}=-5.0V I_C=-10mA f=30MHz	50			MHz



TO-92 Unit: mm





BR:

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Note:

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